

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,018,939 B2
DATED : March 28, 2006
INVENTOR(S) : S. Harma

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 10.

Line 29, should read as follows:

17. A method for making a semiconductor device, comprising the steps of:

providing a semiconductor substrate;

etching a plurality of openings in the semiconductor substrate such that, upon completion of the etch,

at least some of the opening have an organometallic processing residue disposed on a surface

thereof, the processing residue having been formed during the etching process; and

removing at least a portion of the processing residue by contacting the processing residue with a

micellar solution;

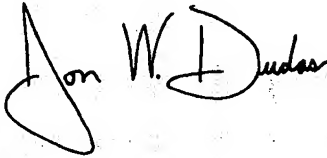
wherein the micellar solution comprises, by weight, about 0.01% to about 1% hydrocarbon surfactant, about 1% to about 10% citric acid, and about 1% to about 10% oxalic acid.

Line 41, should read as follows:

18. The method of claim 17, wherein the micellar solution further comprises, by weight, about 0.01% to about 1% hydrocarbon surfactant, about 1% to about 10% citric acid, about 1% to about 10% oxalic acid, and about 1% to about 10% ethylene glycol monobutyl ether (EGMBE).

Signed and Sealed this

Thirtieth Day of May, 2006

A handwritten signature in black ink, reading "Jon W. Dudas", is written over a rectangular dashed-line box. The signature is stylized, with the first name "Jon" and last name "Dudas" clearly legible, and "W." in the middle.

JON W. DUDAS

Director of the United States Patent and Trademark Office